



**TO-126 Plastic-Encapsulate Transistors**

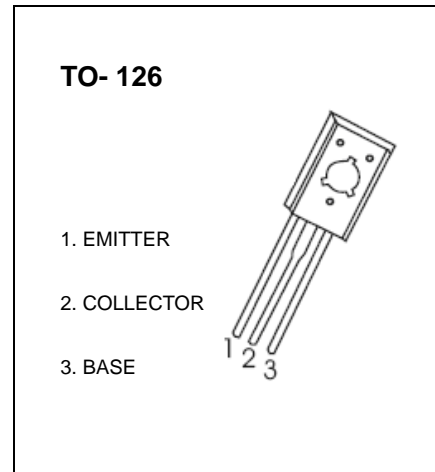
**2SB649/2SB649A TRANSISTOR (PNP)**

**FEATURES**

- Low Frequency Power Amplifier Complementary Pair with 2SD669/A

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-180	V
V <sub>CEO</sub>	Collector-Emitter Voltage		
	2SB649	-120	V
	2SB649A	-160	
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current –Continuous	-1.5	A
P <sub>C</sub>	Collector Power Dissipation	1	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C



**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -1mA, I <sub>E</sub> = 0	-180			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -10mA, I <sub>B</sub> = 0	2SB649	-120		V
			2SB649A	-160		
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -1mA, I <sub>C</sub> = 0	-5			V
Collector cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = -160V, I <sub>E</sub> = 0			-10	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -4V, I <sub>C</sub> = 0			-10	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -150mA	2SB649	60	320	
			2SB649A	60	200	
	h <sub>FE(2)</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -500mA		30		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA			-1	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -150mA			-1.5	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -150mA		140		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f = 1MHz		27		pF

**CLASSIFICATION OF h<sub>FE(1)</sub>**

Rank		B	C	D
Range	2SB649	60-120	100-200	160-320
	2SB649A	60-120	100-200	